



CST3415E P-Ch 20V Fast Switching MOSFETs

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST3415E Product Summary



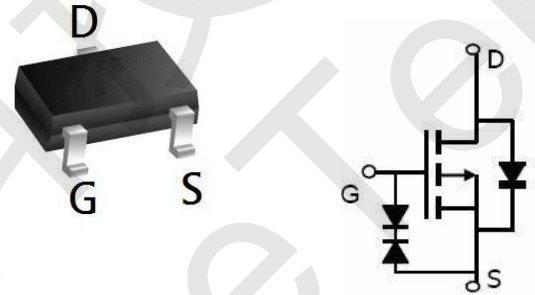
BVDSS	RDSON	ID
-20V	29mΩ	-5.0A

CST3415E Description

The CST3415E is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST3415E meet the RoHS and Green Product requirement with full function reliability approved. ESD Rating: 2500V HBM

CST3415E SOT23 Pin Configuration



CST3415E Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-20		V
V_{GS}	Gate-Source Voltage	±10		V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-5.	-4.	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-4.	-3.7	A
I_{DM}	Pulsed Drain Current ²	-18		A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.32	1	W
T_{STG}	Storage Temperature Range	-55 to 150		°C
T_J	Operating Junction Temperature Range	-55 to 150		°C

CST3415E Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	125	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	95	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	°C/W



CST3415E P-Ch 20V Fast Switching MOSFETs

CST3415E Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±10V	-	-	±10	uA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.7	-1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =-4.5V, I _D =-4A	-	29	40	mΩ
		V _{GS} =-2.5V, I _D =-3A	-	40	56	
Dynamic Characteristics www.power-mos.com						
C _{iss}	Input Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz	-	289	-	pF
C _{oss}	Output Capacitance		-	98	-	pF
C _{rss}	Reverse Transfer Capacitance		-	22	-	pF
Q _g	Total Gate Charge	V _{DS} = -10V, I _D = -4.1A, V _{GS} = -4.5V	-	9	-	nC
Q _{gs}	Gate-Source Charge		-	1	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	2.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -10V, R _G = 1Ω, V _{GEN} =-4.5V, R _L =1.2Ω	-	12	-	ns
t _r	Turn-on Rise Time		-	35	-	ns
t _{d(off)}	Turn-off Delay Time		-	30	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4.1	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16.4	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -4.1A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycles≤2%



CST3415E Typical Performance Characteristics

Figure 1: Output Characteristics

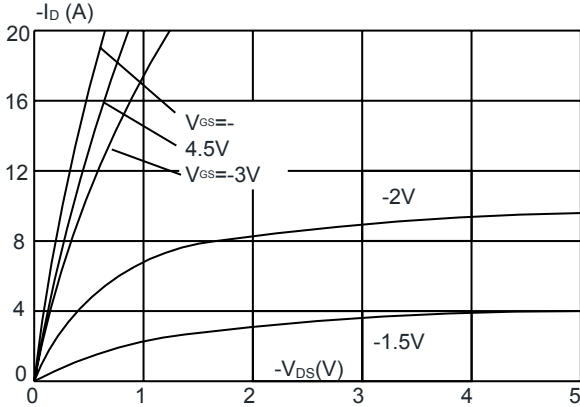


Figure 2: Typical Transfer Characteristics

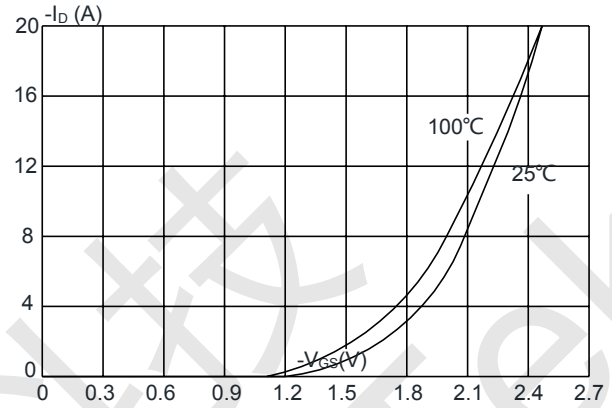


Figure 3: On-resistance vs. Drain Current

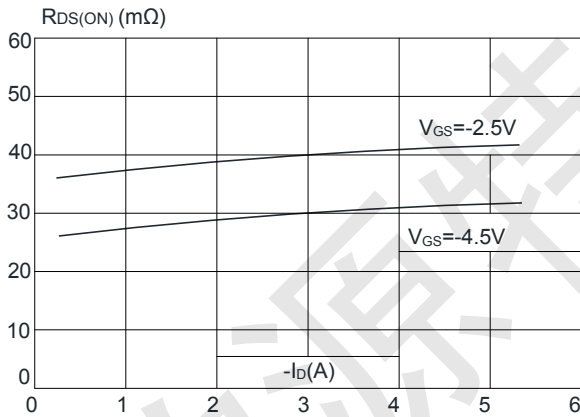


Figure 4: Body Diode Characteristics

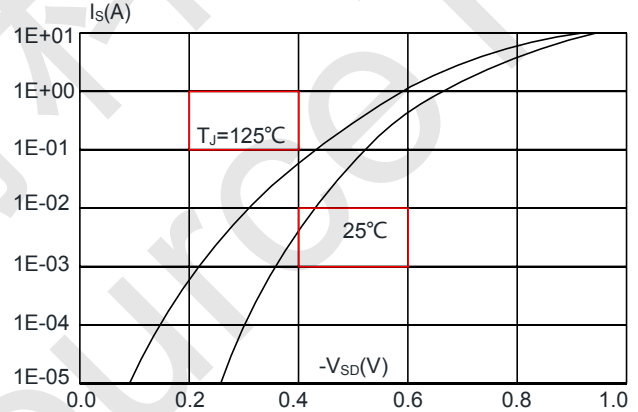


Figure 5: Gate Charge Characteristics

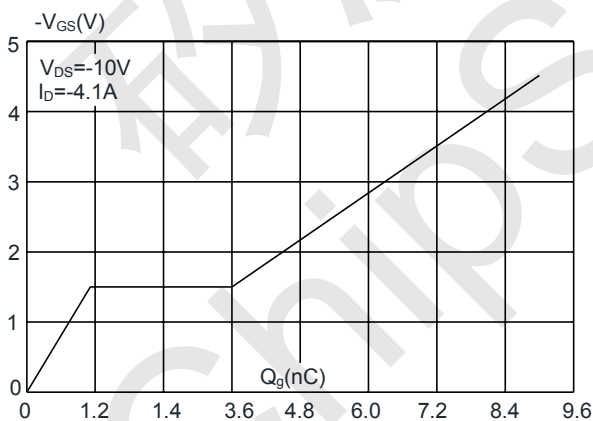
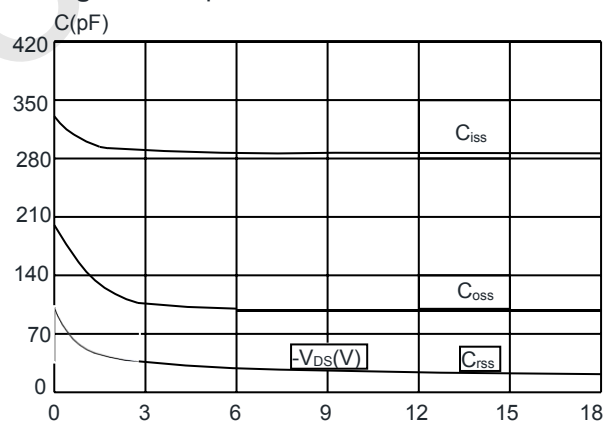


Figure 6: Capacitance Characteristics





CST3415E P-Ch 20V Fast Switching MOSFETs

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

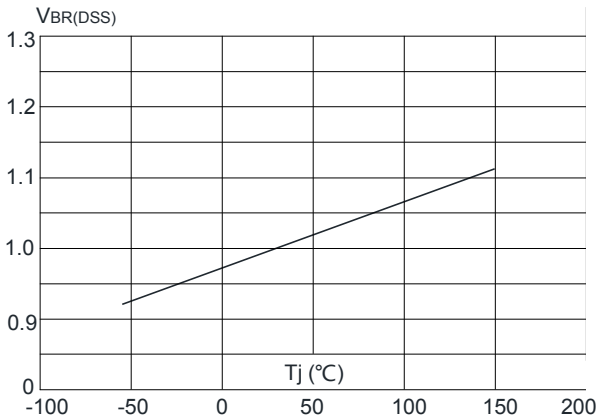


Figure 8: Normalized on Resistance vs. Junction Temperature

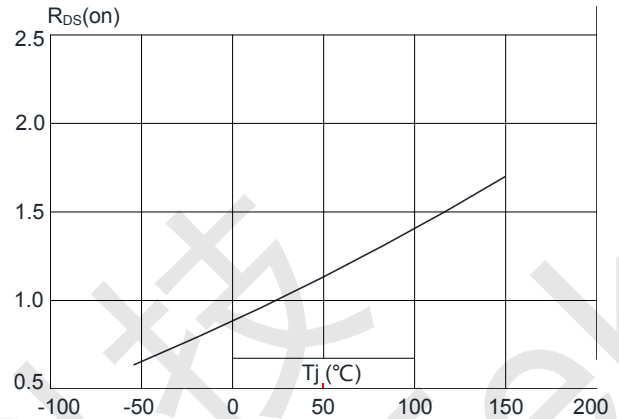


Figure 9: Maximum Safe Operating Area

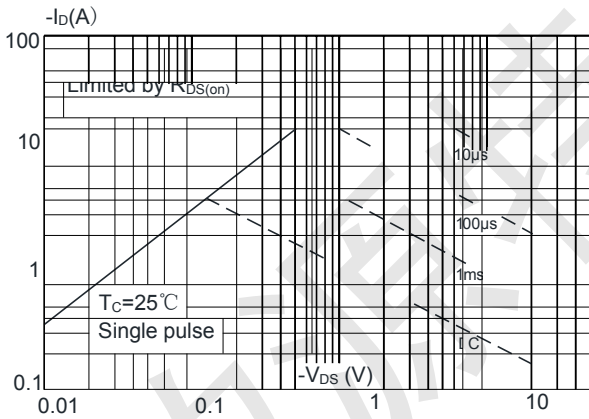


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

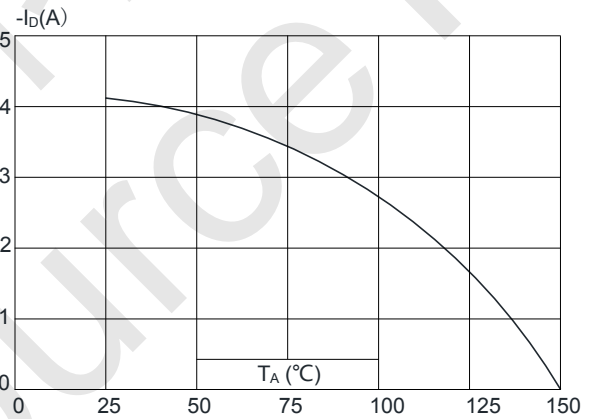
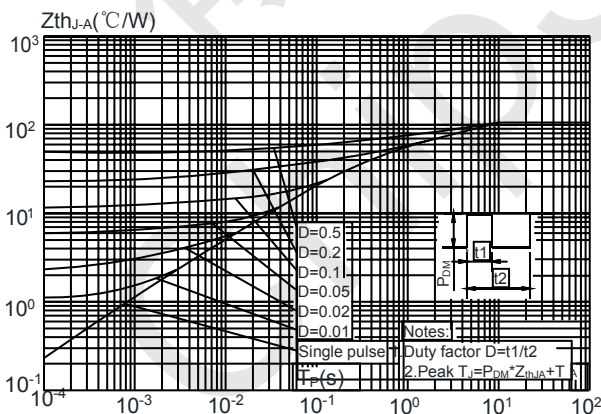
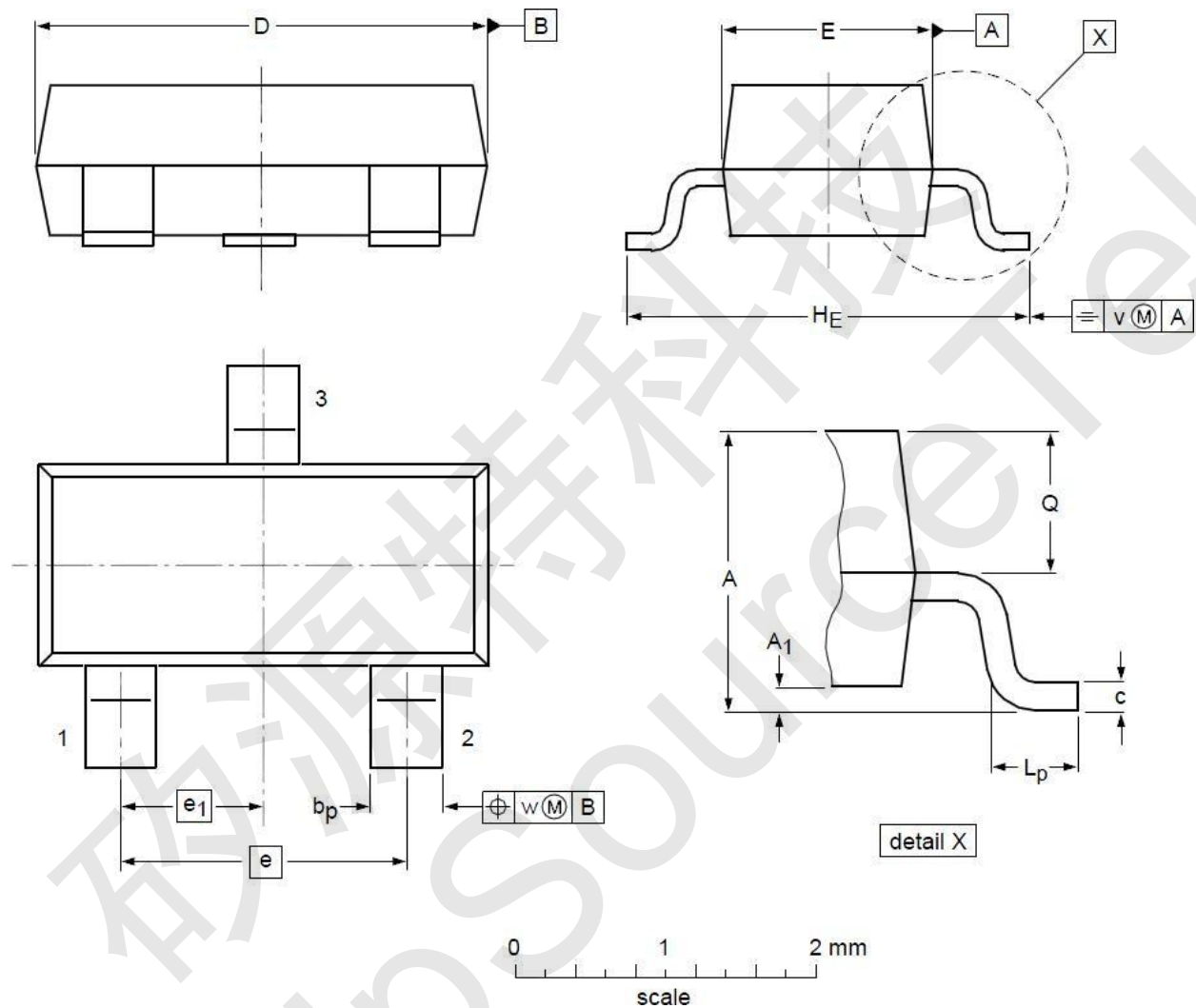


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST3415E SOT23 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				